

SUPPORTING INFORMATION

Synergistic optimization of thermoelectric performance of Sb doped GeTe with strained domain and domain boundaries

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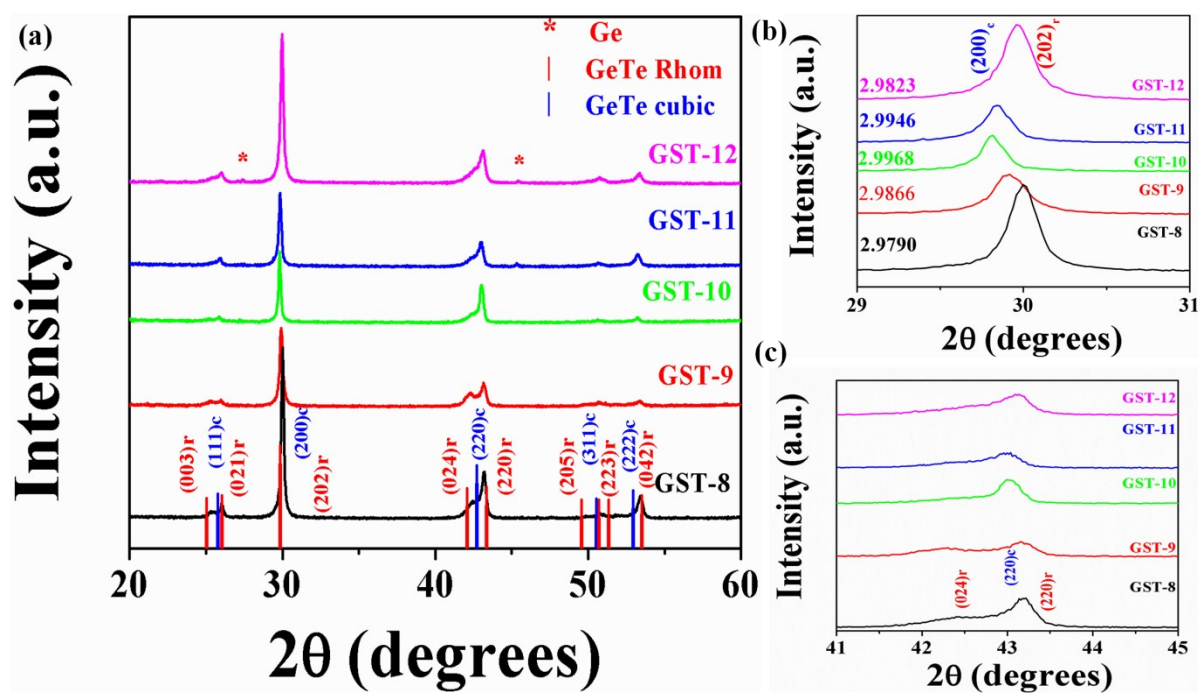


Figure S1: (a) XRD patterns for the GST compounds. (b) (202)_r peak shifting, and (c) characteristic peaks between 40-45 °.

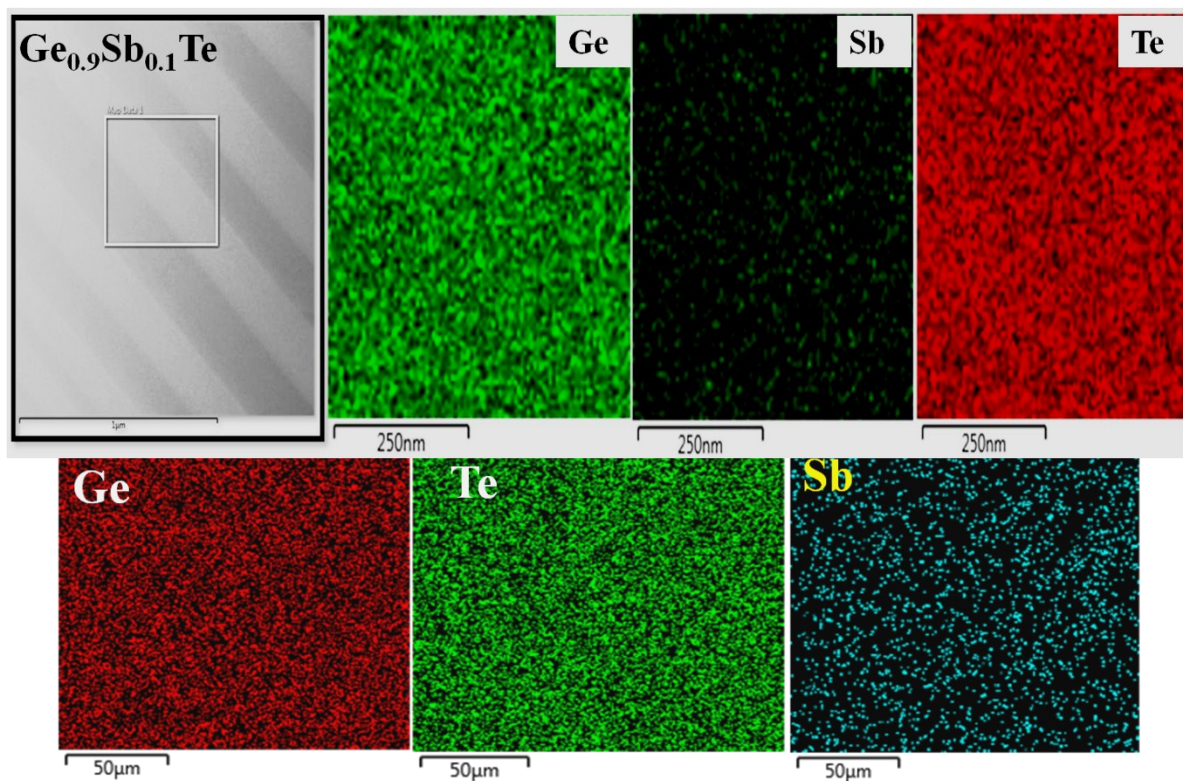


Figure S2: FE-SEM image for the elemental mapping of $\text{Ge}_{0.9}\text{Sb}_{0.1}\text{Te}$. The individual mapping for Ge, Sb, and Te confirms that no Ge precipitate present in the 50 μ length scale.

Figure S3: TEM image for the elemental mapping for $\text{Ge}_{0.9}\text{Sb}_{0.1}\text{Te}$ at 250 nm scale, no Ge precipitants is confirmed.

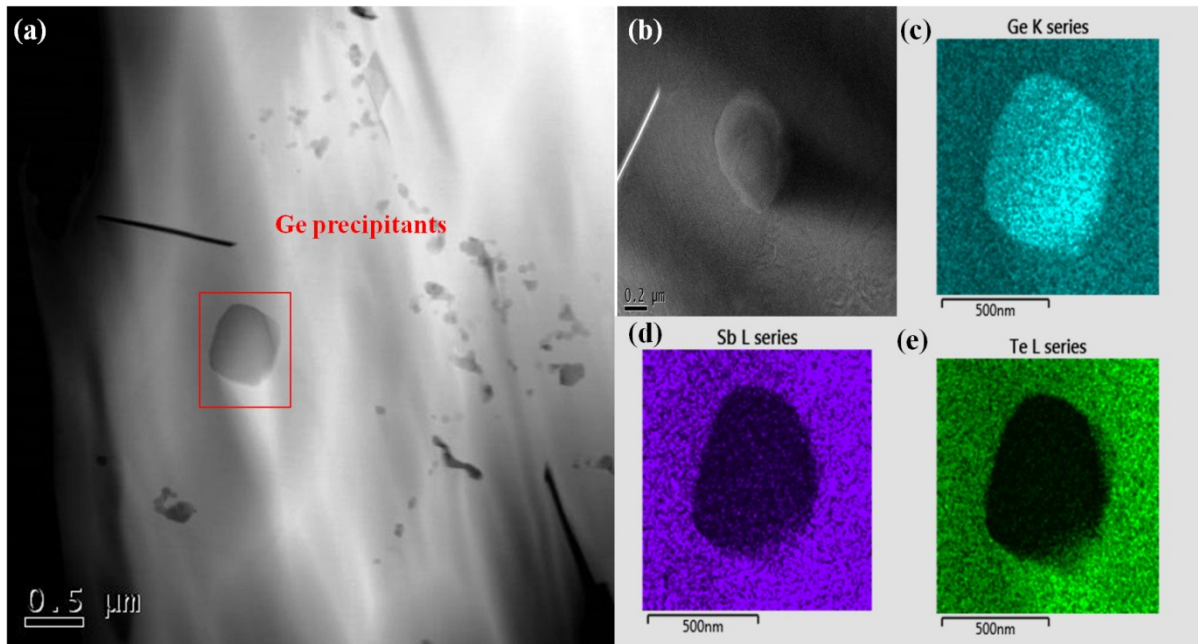


Figure S4: TEM image and elemental mapping of $\text{Ge}_{0.88}\text{Sb}_{0.12}\text{Te}$. Ge precipitate is identified, as verified from (c) to (e).

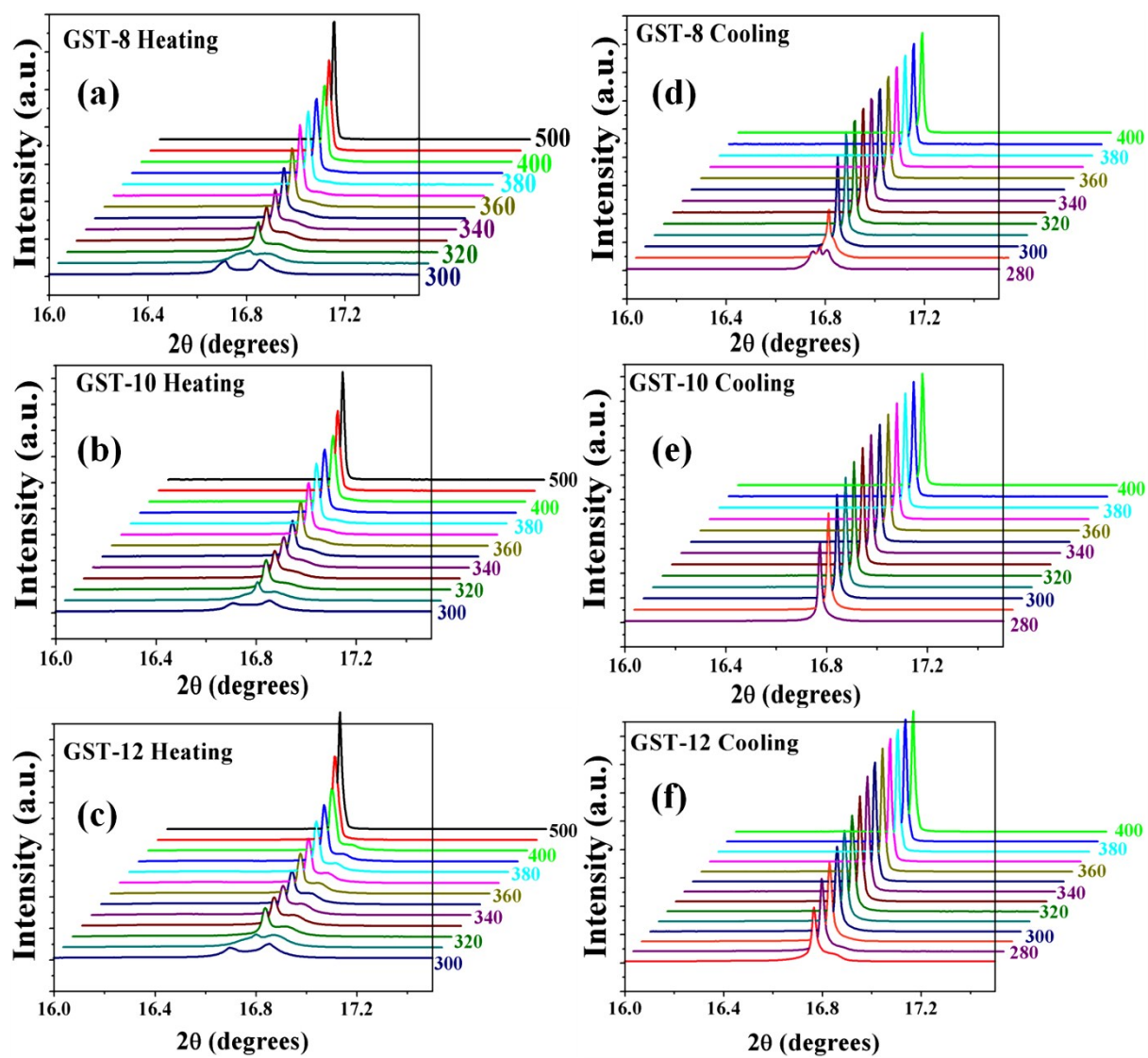


Figure S5: High temperature synchrotron XRD analysis for the GST- 8, 10, and 12 samples upon (a)-(c) warming and (d)-(f) cooling. The wavelength of the incident synchrotron X-ray is 0.62 Å.

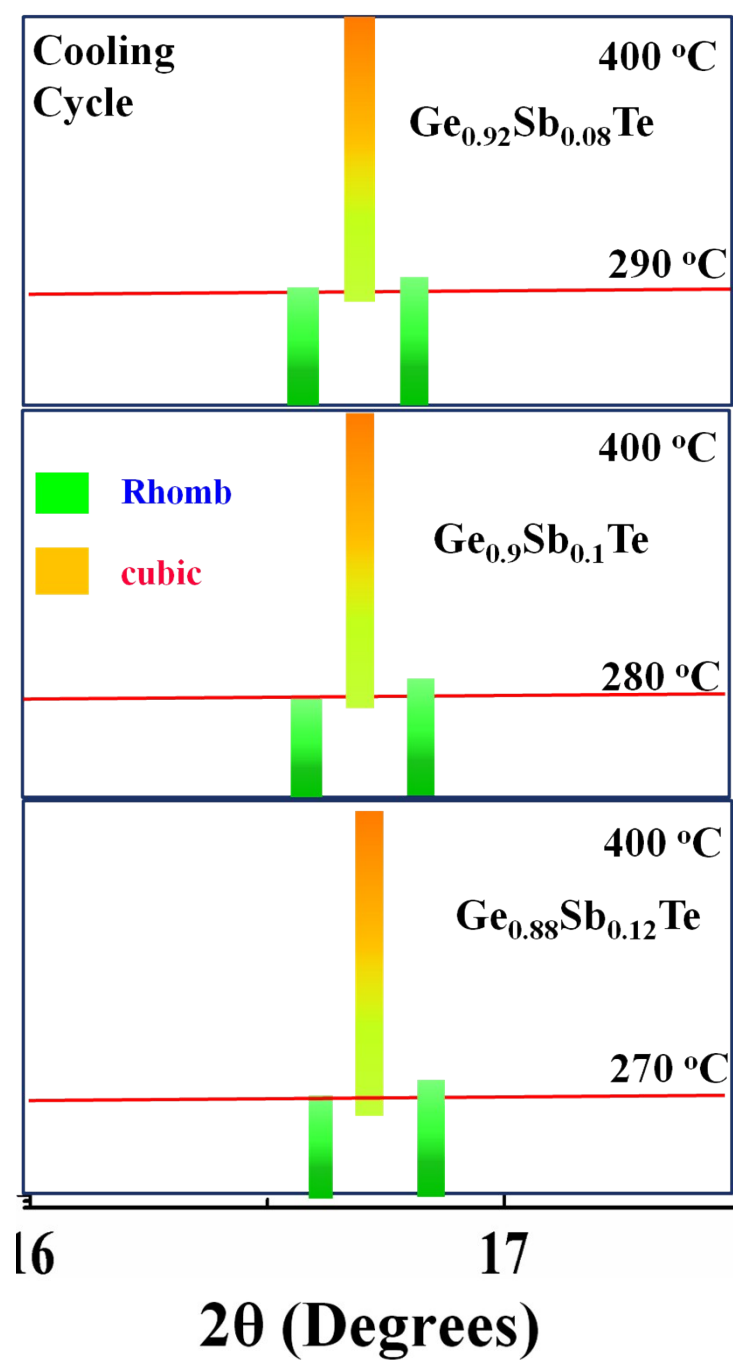


Figure S6: Based on the cooling cycle data shown in Fig. 5S, the temperature and Sb doping dependence is analysed to show the evolution of rhombohedral-to-cubic reversible phase transformation.

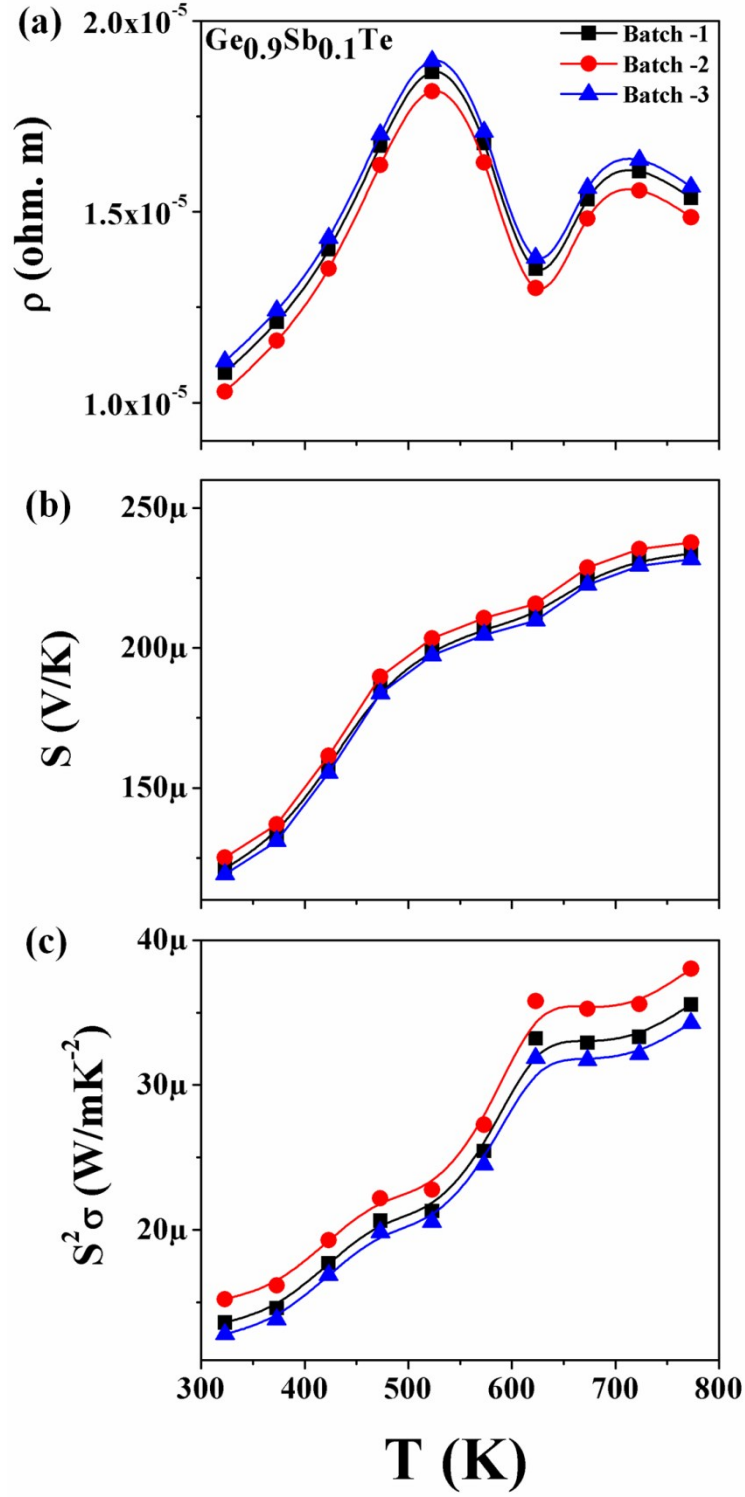


Figure S7: The reproducibility has been checked using two more separately prepared batches of $\text{Ge}_{0.9}\text{Sb}_{0.1}\text{Te}$ -900. Temperature dependence of (a) electrical conductivity, (b) Seebeck coefficient, and (c) power factor.

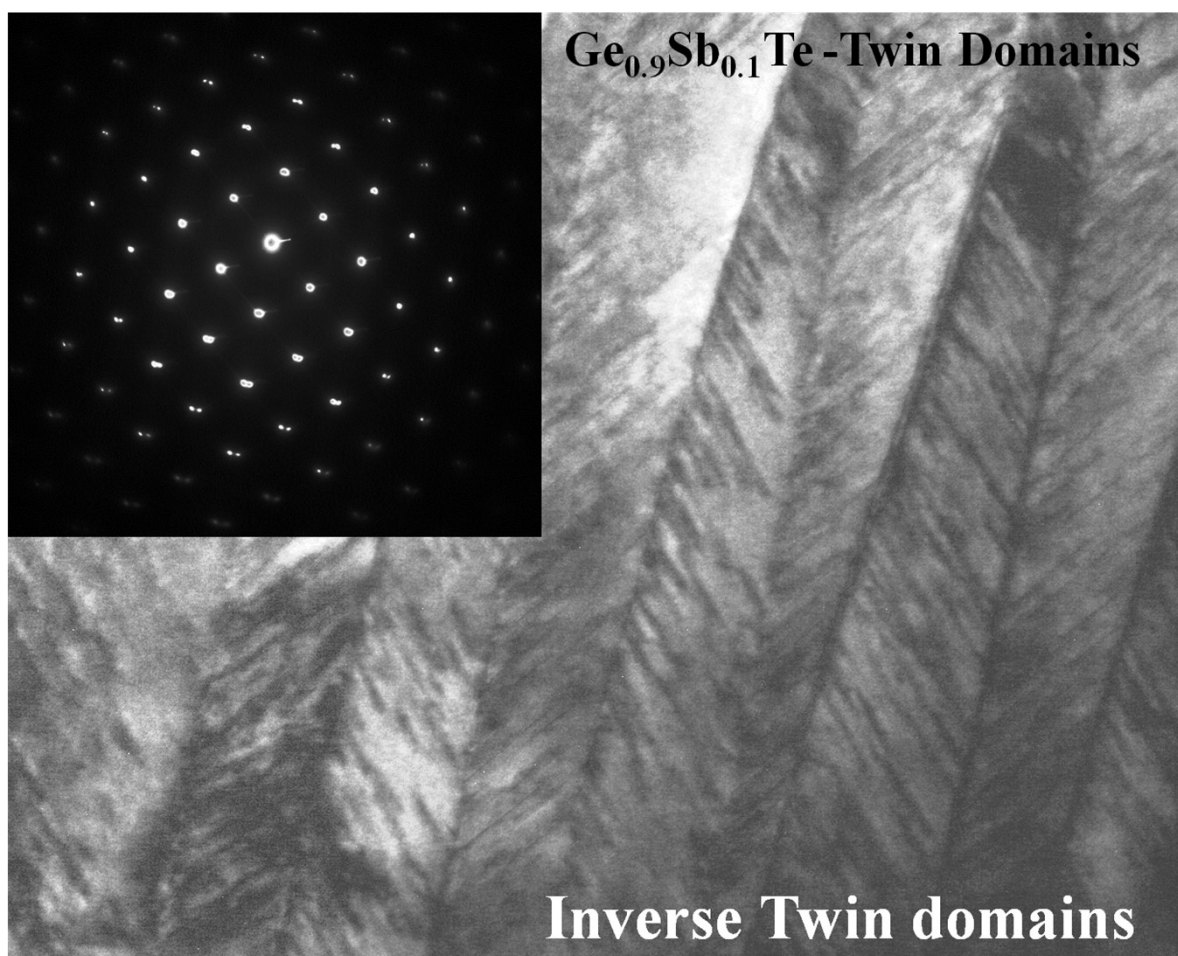


Figure S8: The herringbone structure of Ge_{0.9}Sb_{0.1}Te-900 shows twin domains and inverse-twin domain. The inset of shows doublet in the SAED pattern originated from the twin domain.

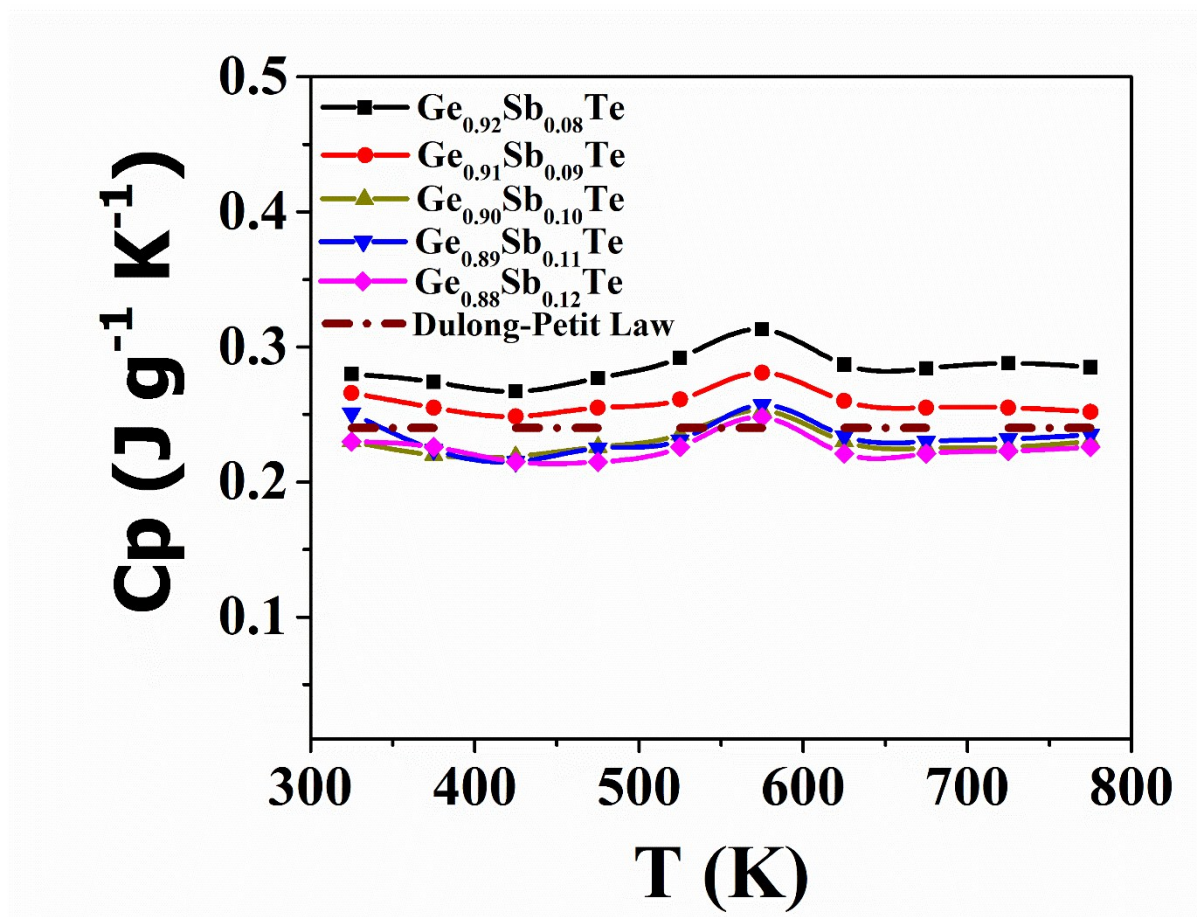


Figure S9. Dulong-Petit C_p and experimentally measured C_p as a function of temperature.